

2N5060 THRU 2N5064

**SILICON CONTROLLED RECTIFIER  
0.8 AMP, 30 THRU 200 VOLTS**



**TO-92 CASE**

**Central**<sup>TM</sup>  
**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N5060 series types are epoxy molded Silicon Controlled Rectifiers designed for control systems and sensing circuit applications.

**MARKING CODE: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

	SYMBOL	2N5060	2N5061	2N5062	2N5063	2N5064	UNITS
Peak Repetitive Off-State Voltage	$V_{DRM}, V_{RRM}$	30	60	100	150	200	V
RMS On-State Current ( $T_C=60^\circ\text{C}$ )	$I_{T(RMS)}$			0.8			A
Peak One Cycle Surge	$I_{TSM}$			10			A
Peak Forward Gate Current ( $t_p=20\mu\text{s}$ )	$I_{GM}$			1.0			A
Peak Reverse Gate Voltage	$V_{GM}$			5.0			V
Peak Gate Power Dissipation	$P_{GM}$			2.0			W
Average Gate Power Dissipation ( $t=20\mu\text{s}$ )	$P_G (AV)$			0.1			W
Storage Temperature	$T_{stg}$			-40 to +150			$^\circ\text{C}$
Junction Temperature	$T_J$			-40 to +125			$^\circ\text{C}$

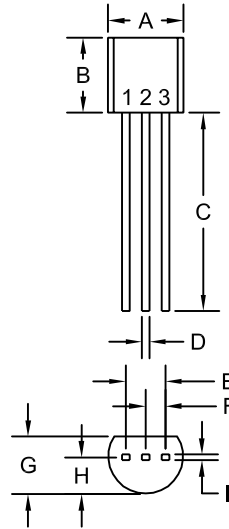
**ELECTRICAL CHARACTERISTICS:** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{DRM}, I_{RRM}$	Rated $V_{DRM}, V_{RRM}, R_{GK}=1\text{K}\Omega$			1.0	$\mu\text{A}$
$I_{DRM}, I_{RRM}$	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}, R_{GK}=1\text{K}\Omega$			50	$\mu\text{A}$
$I_{GT}$	$V_D=7.0\text{V}, R_L=100\Omega, R_{GK}=1\text{K}\Omega$			200	$\mu\text{A}$
$I_{GT}$	$V_D=7.0\text{V}, R_L=100\Omega, R_{GK}=1\text{K}\Omega, T_C=-65^\circ\text{C}$			350	$\mu\text{A}$
$I_H$	$R_{GK}=1\text{K}\Omega$			5.0	mA
$I_H$	$R_{GK}=1\text{K}\Omega, T_C=-65^\circ\text{C}$			10	mA
$V_{GT}$	$V_D=7.0\text{V}, R_L=100\Omega$			0.8	V
$V_{GT}$	$V_D=7.0\text{V}, R_L=100\Omega, T_C=-65^\circ\text{C}$			1.2	V
$V_{GT}$	$V_D=7.0\text{V}, R_L=100\Omega, T_C=125^\circ\text{C}$	0.1			V
$V_{TM}$	$I_{TM}=1.2\text{A}$			1.7	V
dv/dt	$V_D=0.67\text{V} \times V_{DRM}, T_C=125^\circ\text{C}, R_{GK}=1\text{K}\Omega$		30		V/ $\mu\text{s}$
$t_q$	$V_D=0.67\text{V} \times V_{DRM}, T_C=125^\circ\text{C}, R_{GK}=1\text{K}\Omega$			200	$\mu\text{s}$

R4 (25-August 2004)

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**TO-92 CASE - MECHANICAL OUTLINE**



R1

**LEAD CODE:**

- 1) CATHODE
- 2) GATE
- 3) ANODE

**MARKING CODE:**

**FULL PART NUMBER**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)



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